CORRECTION

Correction to: Theoretical prediction of radiation-enhanced diffusion behavior in nickel under self-ion irradiation

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In the original publication, there is a mistake in Eq. (9) and its explanations (Sect. 2.2). The correction is as follows:

$$D_v = \alpha a_0^2 v_0 \exp(-H_v^m / k_B T) \quad (9)$$

where a_0 is the lattice constant and v_0 is the attempt frequency for vacancy exchange [1, 27], k_B is the Boltzmann's constant. For a fcc lattice, each atom has 12 nearest neighbors ($z = 12$), and the jump distance is $Aa_0 = \frac{1}{\sqrt{2}}a_0$. Then, we have $\alpha = 1/6zA^2 = 1$ [1].

Furthermore, the production rate of freely migrating defects, K_0/K , used in this work (Table 1) should be 0.03 (assumed).

The authors would like to apologize for the inconvenience caused.

The original article can be found online at <https://doi.org/10.1007/s41365-020-00791-w>.

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